MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)		-0.5 to +7.0	V
V _{IN}	DC Input Voltage (Referenced to GND)		–0.5 to V _{CC} +0.5	V
V _{OUT}	DC Output Voltage (Referenced to GND) (Note 1)		-0.5 to V _{CC} +0.5	V
I _{IK}	DC Input Diode Current		±20	mA
I _{OK}	DC Output Diode Current		±50	mA
I _{OUT}	DC Output Sink/Source Current		±50	mA
I _{CC}	DC Supply Current, per Output Pin		±50	mA
I _{GND}	DC Ground Current, per Output Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		140	°C
θ_{JA}	Thermal Resistance (Note 2)	SOIC TSSOP	65.8 110.7	°C/W
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating Oxygen Index	k: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body M Machine M Charged Device M	lodel (Note 4)	> 2000 > 200 > 1000	V
I _{Latchup}	Latchup Performance Above V _{CC} and Below GND at 8	35°C (Note 6)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. I_O absolute maximum rating must be observed.
- The package thermal impedance is calculated in accordance with JESD 51–7.
- 3. Tested to EIA/JESD22-A114-A.
- 4. Tested to EIA/JESD22-A115-A.
- Tested to JESD22-C101-A.
- 6. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Тур	Max	Unit
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Complex Voltage	′AC	2.0	5.0	6.0	V
V _{CC}	Supply Voltage	'ACT	4.5	5.0	5.5	V
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Ref. to GND)		0	_	V _{CC}	V
		V _{CC} @ 3.0 V	-	150	_	
t _r , t _f	Input Rise and Fall Time (Note 7) 'AC Devices except Schmitt Inputs	V _{CC} @ 4.5 V	-	40	_	ns/V
	The Borness except estimat inputs	V _{CC} @ 5.5 V	-	25	_	
	Input Rise and Fall Time (Note 8)	V _{CC} @ 4.5 V	-	10	_	2011
t _r , t _f	'ACT Devices except Schmitt Inputs	-	8.0	_	ns/V	
T _A	Operating Ambient Temperature Range			25	85	°C
I _{OH}	Output Current – High			_	-24	mA
I _{OL}	Output Current – Low			_	24	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- V_{IN} from 30% to 70% V_{CC}; see individual Data Sheets for devices that differ from the typical input rise and fall times.
 V_{IN} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

			74	AC	74AC				
Symbol	Parameter	V _{CC}	I A = +25°G		T _A = +25°C		T _A =-40°C to +85°C	Unit	Conditions
		(V)	Тур	Gu	aranteed Limits				
V _{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V		
V _{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V		
V _{OH}	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	I _{OUT} = -50 μA		
		3.0 4.5 5.5	- - -	2.56 3.86 4.86	2.46 3.76 4.76	V	*V _{IN} = V _{IL} or V _{IH} -12 mA I _{OH} -24 mA -24 mA		
V _{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	٧	I _{OUT} = 50 μA		
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V	* V _{IN} = V _{IL} or V _{IH} 12 mA $_{\rm IOL}$ 24 mA $_{\rm 24}$ mA		
I _{IN}	Maximum Input Leakage Current	5.5	_	±0.1	±1.0	μΑ	$V_I = V_{CC}$, GND		
I _{OZ}	Maximum 3-State Current	5.5	_	±0.5	±5.0	μΑ	$\begin{aligned} &V_{I}\left(OE\right) = V_{IL}, \ V_{IH} \\ &V_{I} = V_{CC}, \ GND \\ &V_{O} = V_{CC}, \ GND \end{aligned}$		
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Ma		
I _{OHD}	Output Current	5.5	-	-	- 75	mA	V _{OHD} = 3.85 V Mi		
I _{CC}	Maximum Quiescent Supply Current	5.5	_	8.0	80	μΑ	V _{IN} = V _{CC} or GNE		

 $^{^{\}star}\text{All}$ outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

NOTE: I $_{\rm IN}$ and I $_{\rm CC}$ @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V $_{\rm CC}$.

AC CHARACTERISTICS (For Figures and Waveforms – See AND8277/D at www.onsemi.com)

				74AC		74.	AC		
Symbol	Parameter		V_{CC}^* $T_A = +25^{\circ}C$ $C_L = 50 \text{ pF}$		$T_A = -40$ °C to +85°C $C_L = 50 \text{ pF}$		Unit	Fig. No.	
			Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay Data to Output	3.3 5.0	1.5 1.5	6.0 4.5	8.0 6.5	1.0 1.0	9.0 7.0	ns	3–5
t _{PHL}	Propagation Delay Data to Output	3.3 5.0	1.5 1.5	5.5 4.5	8.0 6.0	1.0 1.0	8.5 6.5	ns	3–5
t _{PZH}	Output Enable Time	3.3 5.0	1.5 1.5	6.0 5.0	10.5 7.0	1.0 1.0	11.0 8.0	ns	3–7
t _{PZL}	Output Enable Time	3.3 5.0	1.5 1.5	7.0 5.5	10.0 8.0	1.0 1.0	11.0 8.5	ns	3–8
t _{PHZ}	Output Disable Time	3.3 5.0	1.5 1.5	7.0 6.5	10.0 9.0	1.0 1.0	10.5 9.5	ns	3–7
t _{PLZ}	Output Disable Time	3.3 5.0	1.5 1.5	7.5 6.5	10.5 9.0	1.0 1.0	11.5 9.5	ns	3–8

 $^{^{\}ast}$ Voltage Range 3.3 V is 3.3 V ± 0.3 V. Voltage Range 5.0 V is 5.0 V ± 0.5 V.

DC CHARACTERISTICS

			74	ACT	74ACT			
Symbol	Parameter	V _{CC}	T _A =	$T_A = +25^{\circ}C$ $T_A = -40^{\circ}C$ to		Unit	Conditions	
		(V)	Typ Guarante		aranteed Limits			
V_{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V	
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V	
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I _{OUT} = -50 μA	
		4.5 5.5	_ _	3.86 4.86	3.76 4.76	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ I_{OH} -24 mA -24 mA	
V_{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I _{OUT} = 50 μA	
		4.5 5.5	_ _	0.36 0.36	0.44 0.44	V	$^{*}V_{IN} = V_{IL} \text{ or } V_{IH}$ $^{24} \text{ mA}$ ^{1}OL $^{24} \text{ mA}$	
I _{IN}	Maximum Input Leakage Current	5.5	_	±0.1	±1.0	μΑ	V _I = V _{CC} , GND	
ΔI_{CCT}	Additional Max. I _{CC} /Input	5.5	0.6	_	1.5	mA	$V_{I} = V_{CC} - 2.1 \text{ V}$	
I _{OZ}	Maximum 3–State Current	5.5	-	±0.5	±5.0	μΑ	V_{I} (OE) = V_{IL} , V_{IH} V_{I} = V_{CC} , GND V_{O} = V_{CC} , GND	
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max	
I _{OHD}	Output Current	5.5	-	_	-75	mA	V _{OHD} = 3.85 V Min	
Icc	Maximum Quiescent Supply Current	5.5	_	8.0	80	μΑ	V _{IN} = V _{CC} or GND	

 $^{^\}star\text{All}$ outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS (For Figures and Waveforms – See Section 3 of the ON Semiconductor FACT Data Book, DL138/D)

	Parameter		74ACT			74ACT			
Symbol				Γ _A = +25°(C _L = 50 pF		T _A = - to +8 C _L = 8	35°C	Unit	Fig. No.
	!		Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay Data to Output	5.0	1.5	6.0	8.5	1.5	9.5	ns	3–5
t _{PHL}	Propagation Delay Data to Output	5.0	1.5	5.5	7.5	1.5	8.5	ns	3–5
t _{PZH}	Output Enable Time	5.0	1.5	7.0	8.5	1.0	9.5	ns	3–7
t _{PZL}	Output Enable Time	5.0	2.0	7.0	9.5	1.5	10.5	ns	3–8
t _{PHZ}	Output Disable Time	5.0	2.0	8.0	9.5	2.0	10.5	ns	3–7
t _{PLZ}	Output Disable Time	5.0	2.5	6.5	10.0	2.0	10.5	ns	3–8

^{*}Voltage Range 5.0 V is 5.0 V ± 0.5 V.

CAPACITANCE

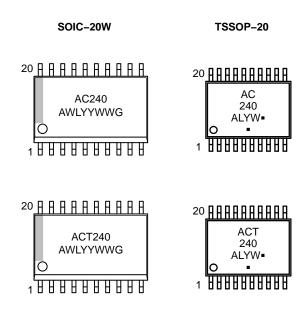
Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	45	рF	V _{CC} = 5.0 V

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74AC240DWG		38 Units / Rail
MC74AC240DWR2G	SOIC-20	1000 / Tape & Reel
MC74ACT240DWG	(Pb-Free)	38 Units / Rail
MC74ACT240DWR2G		1000 / Tape & Reel
MC74AC240DTR2G	TSSOP-20	2500 / Tape & Reel
MC74ACT240DTR2G	(Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS



A = Assembly Location

WL, L = Wafer Lot YY, Y = Year

WW, W = Work Week
G or ■ = Pb–Free Package

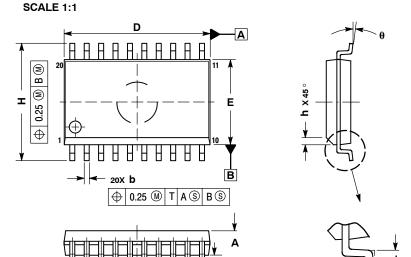
(Note: Microdot may be in either location)





SOIC-20 WB CASE 751D-05 **ISSUE H**

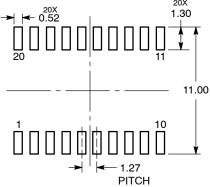
DATE 22 APR 2015



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

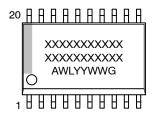
	MILLIMETERS						
DIM	MIN	MAX					
Α	2.35	2.65					
A1	0.10	0.25					
b	0.35	0.49					
С	0.23	0.32					
D	12.65	12.95					
E	7.40	7.60					
е	1.27	BSC					
Н	10.05	10.55					
h	0.25	0.75					
L	0.50	0.90					
A	0 °	7 °					

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

0.100 (0.004)

16X

1.26

SOLDERING FOOTPRINT

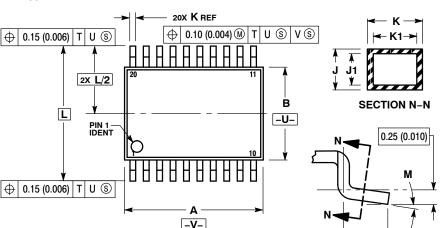
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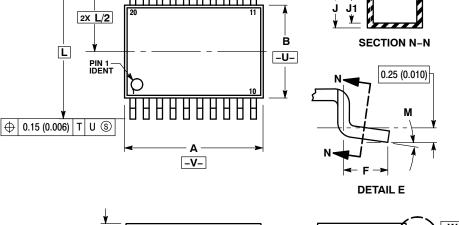
-T- SEATING

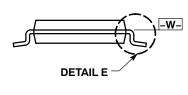


TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016







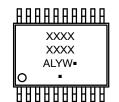
NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252	BSC	
M	0°	8°	0°	8°	

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	TSSOP-20 WB		PAGE 1 OF 1				

DIMENSIONS: MILLIMETERS

0.65

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